

MAXIMUM RATINGS

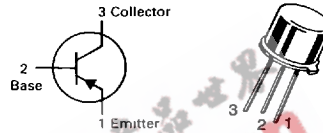
Rating	Symbol	2N4032	2N4033	Unit
Collector-Emitter Voltage	V_{CEO}	-60	-80	Vdc
Collector-Base Voltage	V_{CBO}	-60	-80	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	-5.0	Vdc
Collector Current — Continuous	I_C	-1.0		Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	0.8		W
		4.56		
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	4.0		W
		22.8		
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	140	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	25	°C/W

**2N4032
2N4033**

**CASE 79-04, STYLE 1
TO-39 (TO-205AD)**



**GENERAL PURPOSE
TRANSISTORS**
PNP SILICON

Refer to 2N4405 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = -10\text{ mA}$)	$V_{(BR)CEO}$	-60 -80	—	V
Collector-Base Breakdown Voltage ($I_C = -10\ \mu\text{A}$)	$V_{(BR)CBO}$	-60 -80	—	V
Emitter-Base Breakdown Voltage ($I_E = -10\ \mu\text{A}$)	$V_{(BR)EBO}$	-5.0	—	V
Collector Cutoff Current ($V_{CB} = -50\text{ V}$) ($V_{CB} = -60\text{ V}$) ($V_{CB} = -50\text{ V}, T_A = 150^\circ\text{C}$) ($V_{CB} = -60\text{ V}, T_A = 150^\circ\text{C}$)	I_{CBO}	—	-50 -50 -50 -50	nA μA
Emitter Cutoff Current ($V_{EB} = -5.0\text{ V}$)	I_{EBO}	—	-10	μA
ON CHARACTERISTICS				
DC Current Gain ($I_C = -100\text{ mA}, V_{CE} = -5.0\text{ V}, @ -55^\circ\text{C}$)(1)	h_{FE}	40	—	—
($I_C = -100\ \mu\text{A}, V_{CE} = -5.0\text{ V}$)		75	—	
($I_C = -100\text{ mA}, V_{CE} = -5.0\text{ V}$)(1)		100	300	
($I_C = -500\text{ mA}, V_{CE} = -5.0\text{ V}$)(1)		70	—	
($I_C = -1.0\text{ A}, V_{CE} = -5.0\text{ V}$)F(1)		40 25	—	

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2N4032 2N4033

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Saturation Voltage(1) ($I_C = -150\text{ mA}$, $I_B = -15\text{ mA}$) ($I_C = -500\text{ mA}$, $I_B = -50\text{ mA}$) ($I_C = -1.0\text{ A}$, $I_B = -100\text{ mA}$)	$V_{CE(sat)}$	—	-0.15 -0.50 -1.0	V
Base-Emitter Saturation Voltage(1) ($I_C = -150\text{ mA}$, $I_B = -15\text{ mA}$)	$V_{BE(sat)}$	—	-0.9	V
Base-Emitter On Voltage ($I_C = -1.0\text{ A}$, $V_{CE} = -1.0\text{ V}$) ($I_C = -500\text{ mA}$, $V_{CE} = -0.5\text{ V}$)(1)	$V_{BE(on)}$	—	-1.2 -1.1	V
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($V_{CE} = -10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	—	20	pF
Input Capacitance ($V_{EB} = -0.5\text{ V}$, $f = 1.0\text{ MHz}$)	C_{ibo}	—	110	pF
Small Signal Current Gain ($I_C = -50\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 100\text{ MHz}$)	h_{fe}	1.5	5.0	—
SWITCHING CHARACTERISTICS				
Storage Time ($I_C = -500\text{ mA}$, $I_{B1} = I_{B2} = -50\text{ mA}$)	t_s	—	350	ns
Turn-On Time ($I_C = -500\text{ mA}$, $I_{B1} = -50\text{ mA}$)	t_{on}	—	100	ns
Fall Time ($I_C = -500\text{ mA}$, $I_{B1} = I_{B2} = -50\text{ mA}$)	t_f	—	50	ns

(1) Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.